



520.36911VX1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): T. ONO, et al
Serial No.: 09/691,119
Filed: October 19, 2000
For: METHOD AND APPARATUS FOR TREATING SURFACE OF SEMICONDUCTOR
Group: 1763
Examiner: A. Olsen

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AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

February 3, 2003

Sir:

The following amendments and remarks are respectfully submitted in connection with the above-identified application in response to the Office Action dated October 3, 2002.

IN THE SPECIFICATION:

Page 19, please amend the paragraph beginning at line 15 as follows:

A₁
A physical quantity which directly exerts an influence on the depth of the microtrench and the selectivity does not relate to the amplitude of V_{pp}, but relates to the ion energy. Since it is difficult to measure the ion energy in practice, the amplitude of V_{pp} is used as an index of the ion energy. The relation between the ion energy and the rf voltage will now be described. When the rf voltage is applied to the stage via a plasma, a DC potential (hereinbelow, referred to as "V_{dc}") is so generated as to attract ions into the stage by causing a current to flow between the earth (generally, a conductive wall serves as the earth) and the electrode. The ions